

TS12A12511 負の信号を扱える 5Ω シングル・チャネル SPDT アナログ・スイッチ

1 特長

- $\pm 2.7\text{V}$ ～ $\pm 6\text{V}$ のデュアル電源
- 2.7V ～ 12V の単一電源
- 5Ω (標準値) のオン抵抗
- 1.6Ω (標準値) のオン抵抗平坦性
- 3.3V 、 5V 互換のデジタル制御入力
- レール・ツー・レールのアナログ信号処理
- 高速な t_{ON} 、 t_{OFF} 時間
- デジタル信号とアナログ信号の両方のアプリケーションに対応
- 小型の 8 リード SOT-23、8 リード MSOP、QFN-8 パッケージ
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22 準拠で ESD 性能を試験済み
 - 人体モデルで $\pm 2000\text{V}$ (A114-B、Class II)
 - 荷電デバイス・モデルで $\pm 1000\text{V}$ (C101)

2 アプリケーション

- 自動テスト機器
- 電力ルーティング
- 通信システム
- データ・アキュイジション・システム
- サンプル・アンド・ホールド・システム
- リレーの代替品
- グリッド・インフラ

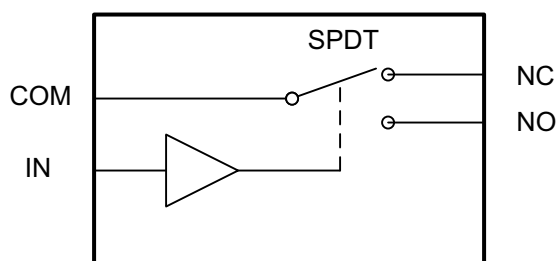
3 概要

TS12A12511 は双方向、シングル・チャネルの単極双投 (SPDT) アナログ・スイッチであり、 $0 \sim 12\text{V}$ または $-6\text{V} \sim 6\text{V}$ の振幅で信号を伝えることができます。このスイッチはオン時にどちらの方向にも等しく電流を流します。また、このデバイスのオン抵抗は 5Ω (標準値) と低く、チャネル間ばらつきは 1Ω 以内です。最大消費電流は $1\mu\text{A}$ 未満であり、 -3dB 帯域幅は 93MHz を超えています。TS12A12511 は Break-Before-Make のスイッチング動作を行うため、チャネルの切り替え時に瞬間的な短絡が起きることを回避できます。このデバイスは、8 リード VSSOP、8 リード SOT-23、および 8 ピン WSON パッケージで供給されます。

パッケージ情報⁽¹⁾

部品番号	パッケージ	本体サイズ (公称)
TS12A12511	DCN (SOT-23, 8)	2.90mm×1.63mm
	DGK (VSSOP, 8)	3.00mm × 3.00mm
	DRJ (WSON, 8)	4.00mm × 4.00mm

- (1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



概略回路図



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision D (January 2019) to Revision E (September 2022)	Page
• 文書全体にわたって表、図、相互参照の採番方法を更新.....	1
• 「アプリケーション」セクションを更新.....	1
• Updated the <i>Leakage Current vs I/O Voltage (Switch ON)</i> and <i>Leakage Current vs I/O Voltage (Switch OFF)</i> figures.....	8
Changes from Revision C (January 2015) to Revision D (January 2019)	Page
• Added Junction temperature to the <i>Absolute Maximum Ratings</i> table.....	4
Changes from Revision B (April 2011) to Revision C (January 2015)	Page
• 「ピン構成および機能」セクション、「ESD 定格」表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加.....	1
Changes from Revision A (May 2010) to Revision B (April 2011)	Page
• Deleted preview status from DGK and DCN packages.....	3

5 Pin Configuration and Functions

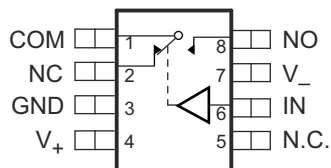


图 5-1. DGK Package, 8-Pin VSSOP (Top View)

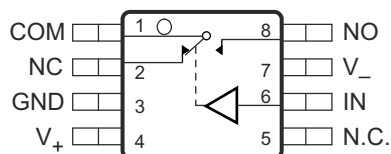
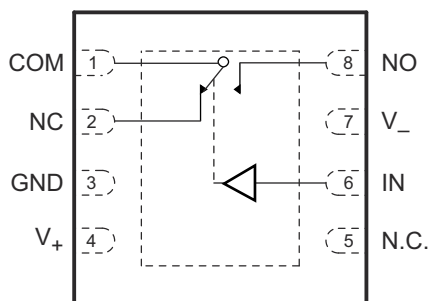


图 5-2. DCN Package, 8-Pin SOT-23 (Top View)



N.C. – Not internally connected NC – Normally closed NO – Normally open
The Exposed Thermal Pad must be electrically connected to V₋ or left floating.

图 5-3. DRJ Package, 8-Pin WSON (Top View)

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
COM	1	I/O	Common. Can be an input or output.
GND	3	—	Ground (0 V) reference
IN	6	I	Logic control input
NC	2	I/O	Normally closed. Can be an input or output.
N.C.	5	—	No connect. Not internally connected.
NO	8	I/O	Normally open. Can be an input or output.
V _{CC}	4	I	Most positive power supply
-V _{CC}	7	I	Most negative power supply. This pin is only used in dual-supply applications and should be tied to ground in single-supply applications.
Thermal pad		—	The Exposed Thermal Pad must be electrically connected to V ₋ or left floating.

(1) I = input, O = output

6 Specifications

6.1 Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ (unless otherwise noted).⁽¹⁾

			MIN	MAX	UNIT
V_{CC} to $-V_{CC}$			0	13	V
V_{CC} to GND			-0.3	13	V
$-V_{CC}$ to GND			-6.5	0.3	V
$V_{I/O}$	Analog inputs	NC, NO, or COM	$-V_{CC} - 0.5$	$V_{CC} + 0.5$	V
I_{IN}	Digital inputs			± 30	mA
$I_{I/O}$	Peak current	NC, NO, or COM		± 100	mA
	Continuous current	NC, NO, or COM		± 50	mA
T_A	Operating temperature		-40	85	$^\circ\text{C}$
T_J	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65	150	$^\circ\text{C}$

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under [セクション 6.3](#) is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	± 2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	± 1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
V_{CC}	0	12	V
$-V_{CC}$	-6	0	V
$V_{I/O}$	$-V_{CC}$	V_{CC}	V
V_{IN}	0	V_{CC}	V

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TS12A12511			UNIT
		DCN	DGK	DRJ	
		8 PINS			
R _{θJA}	Junction-to-ambient thermal resistance	218.4	184.5	47.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	89.9	71.0	48.6	
R _{θJB}	Junction-to-board thermal resistance	144.4	104.5	24.2	
Ψ _{JT}	Junction-to-top characterization parameter	7.8	11.3	1.2	
Ψ _{JB}	Junction-to-board characterization parameter	141.7	103.3	24.4	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	9.0	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics: ± 5 -V Dual Supply

$V_{CC} = 5\text{ V} \pm 10\%$, $-V_{CC} = -5\text{ V} \pm 10\%$, $T_A = -40^\circ\text{C}$ to 85°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A = 25°C			T _A = −40°C to 85°C			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
ANALOG SWITCH									
	Analog signal range					−V _{CC}	V _{CC}		V
R _{ON}	ON-state resistance	V _{NC} = −4.5 V to +4.5 V or V _{NO} = −4.5 V to 4.5 V, I _{COM} = −10 mA; see 7-1		5			5	8	Ω
ΔR _{ON}	ON-state resistance match between channels	V _{NC} = −4.5 V to +4.5 V or V _{NO} = −4.5 V to +4.5 V, I _{COM} = −10 mA		1	1.2			1.6	Ω
R _{ON(flat)}	ON-state resistance flatness	V _{NC} = −3.3 V to +3.3 V or V _{NO} = −3.3 V to +3.3 V, I _{COM} = −10 mA		1.6	2.2			2.2	Ω
LEAKAGE CURRENTS									
I _{NC(OFF)} , I _{NO(OFF)}	OFF leakage current	V _{NC} = −4.5 V to +4.5 V or V _{NO} = −4.5 V to +4.5 V V _{COM} = −4.5 V to +4.5 V; see 7-2	−1	±0.5	1	−50		50	nA
I _{NC(ON)} , I _{NO(ON)}	ON leakage current	V _{NC} = −4.5 V to +4.5 V or V _{NO} = −4.5 V to +4.5 V V _{COM} = open; see 7-3	−1	±0.5	1	−50		50	nA
DIGITAL INPUTS									
V _{INH}	High-level input voltage					2.4		V _{CC}	V
V _{INL}	Low-level input voltage					0		0.8	V
I _{INL} , I _{INH}	Input current	V _{IN} = V _{INL} or V _{INH}		0.005		−1		1	μA
C _{IN}	Control input capacitance			2.5					pF
DYNAMIC ⁽¹⁾									
t _{ON}	Turn-ON time	R _L = 300 Ω, C _L = 35 pF, V _{COM} = 3.3 V; see 7-5		80	95			115	ns
t _{OFF}	Turn-OFF time	R _L = 300 Ω, C _L = 35 pF, V _{COM} = 3.3 V		41	50			56	ns
t _{BBM}	Break-before-make time delay	R _L = 300 Ω, C _L = 35 pF, V _{NC} = V _{NO} = 3.3 V; see 7-6		36		18			ns
Q _C	Charge injection	V _{NC} = V _{NO} = 0 V, R _{GEN} = 0 Ω, C _L = 1 nF; see 7-7		26					pC
O _{ISO}	OFF isolation	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; see 7-8		−70					dB
X _{TALK}	Channel-to-channel crosstalk	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz, see 7-9		−70					dB
BW	Bandwidth −3 dB	R _L = 50 Ω, C _L = 5 pF; see 7-10		93					MHz
THD	Total harmonic distortion	R _L = 600 Ω, C _L = 15pF, V _{NO} = 1V _{RMS} , f = 20 kHz; see 7-11		0.004%					
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	f = 1 MHz; see 7-4		14					pF
C _{COM(ON)} , C _{NC(ON)} , C _{NO(ON)}	COM, NC, NO ON capacitance	f = 1 MHz; see 7-4		60					pF
SUPPLY									
I _{CC}	Positive supply current			0.03				1	μA

(1) Specified by design, not subject to production test.

6.6 Electrical Characteristics: 12-V Single Supply

$V_{CC} = 12\text{ V} \pm 10\%$, $-V_{CC} = 0\text{ V}$, $\text{GND} = 0\text{ V}$, $T_A = -40^\circ\text{C}$ to 85°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A = 25°C			T _A = −40°C to 85°C			UNIT	
			MIN	TYP	MAX	MIN	TYP	MAX		
ANALOG SWITCH										
Analog signal range						0	V _{CC}		V	
R _{on}	ON-state resistance	V _{NC} = 0 V to 10.8 V or V _{NO} = 0 V to 10.8 V, I _{COM} = −10 mA, see 7-1	5				5	8	Ω	
ΔR _{on}	ON-state resistance match between channels	V _{NC} = 0 V to 10.8 V or V _{NO} = 0 V to 10.8 V, I _{COM} = −10 mA	1.6			2.4		2.6	Ω	
R _{on(flat)}	ON-state resistance flatness	V _{NC} = 3.3 V to 7V or V _{NO} = 3.3 V to 7 V, I _{COM} = −10 mA	1.7				1.8	3.2	Ω	
LEAKAGE CURRENTS										
I _{NC(OFF)} , I _{NO(OFF)}	OFF leakage current	V _{NC} = 0 V to 10.8 V or V _{NO} = 0 V to 10.8 V, V _{COM} = 0 V to 10.8 V; see 7-2	−10	±0.5	10	−50			50	nA
I _{NC(ON)} , I _{NO(ON)}	ON leakage current	V _{NC} = 0 V to 10.8V or V _{NO} = 0 V to 10.8 V, V _{COM} = open; see 7-3	−10	±0.5	10	−50			50	nA
DIGITAL INPUTS										
V _{INH}	High-level input voltage					5	V _{CC}		V	
V _{INL}	Low-level input voltage					0	0.8		V	
I _{INL} , I _{INH}	Input current	V _{IN} = V _{INL} or V _{INH}	±0.005			−0.1			0.1	μA
C _{IN}	Digital input capacitance		2.7							pF
DYNAMIC ⁽¹⁾										
t _{ON}	Turn-ON time	R _L = 300 Ω, C _L = 35 pF, V _{COM} = 3.3 V; see 7-5	56			85	110			ns
t _{OFF}	Turn-OFF time	R _L = 300 Ω, C _L = 35 pF, V _{COM} = 3.3 V; see 7-5	25			30	31			ns
t _{BBM}	Break-before-make time delay	R _L = 300 Ω, C _L = 35 pF, V _{NC} = V _{NO} = 3.3 V; see 7-6	30			19				ns
Q _C	Charge injection	R _{GEN} = V _{NC} = V _{NO} = 0 V, R _{GEN} = 0 Ω, C _L = 1 nF; see 7-7	491							pC
O _{ISO}	OFF isolation	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz, see 7-8	−70							dB
X _{TALK}	Channel-to-channel crosstalk	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz, see 7-9	−70							dB
BW	Bandwidth −3 dB	R _L = 50 Ω, C _L = 5 pF, see 7-10	200							MHz
THD	Total harmonic distortion	R _L = 600 Ω, C _L = 15pF, V _{NO} = 1 V _{RMS} , f = 20 kHz; see 7-11	0.04%							
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	f = 1 MHz, see 7-4	14							pF
C _{COM(ON)} , C _{NC(ON)} , C _{NO(ON)}	COM, NC, NO ON capacitance	f = 1 MHz, see 7-4	55							pF
SUPPLY										
I _{CC}	Positive supply current		0.07			1				μA

(1) Specified by design, not subject to production test.

6.7 Electrical Characteristics: 5-V Single Supply

$V_{CC} = 5\text{ V} \pm 10\%$, $-V_{CC} = 0\text{ V}$, $GND = 0\text{ V}$, $T_A = -40^\circ\text{C}$ to 85°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T _A = 25°C			T _A = −40°C to 85°C			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
ANALOG SWITCH									
	Analog signal range					0	V _{CC}	V	
R _{on}	ON-state resistance	V _{NC} = 0 V to 4.5 V or V _{NO} = 0 V to 4.5 V, I _{COM} = −10 mA; see FIG 7-1		8	10		12.5	Ω	
ΔR _{on}	ON-state resistance match between channels	V _{NC} = 0 V to 4.5 V or V _{NO} = 0 V to 4.5 V, I _{COM} = −10 mA		1	1.1		1.5	Ω	
R _{on(flat)}	ON-state resistance flatness	V _{NC} = 0 V to 4.5 V or V _{NO} = 0 V to 4.5 V, I _{COM} = −10 mA		1.3			1.3 2	Ω	
LEAKAGE CURRENTS									
I _{NC(OFF)} , I _{NO(OFF)}	OFF leakage current	V _{NC} = 0 V to 4.5 V or V _{NO} = 0 V to 4.5 V, V _{COM} = 0 V to 4.5 V; see FIG 7-2	−1	±0.5	1	−50	50	nA	
I _{NC(ON)} , I _{NO(ON)}	ON leakage current	V _{NC} = 0 V to 4.5V or V _{NO} = 0 V to 4.5 V, V _{COM} = open; see FIG 7-3	−1	±0.5	1	−50	50	nA	
DIGITAL INPUTS									
V _{INH}	High-level input voltage					2.4	V _{CC}	V	
V _{INL}	Low-level input voltage					0	0.8	V	
I _{INL} , I _{INH}	Input current	V _{IN} = V _{INL} or V _{INH}	0.01			−0.1	0.1	μA	
C _{IN}	Digital input capacitance		2.8					pF	
DYNAMIC ⁽¹⁾									
t _{ON}	Turn-ON time	R _L = 300 Ω, C _L = 35 pF, V _{COM} = 3.3 V; see FIG 7-5		119	145		178	ns	
t _{OFF}	Turn-OFF time	R _L = 300 Ω, C _L = 35 pF, V _{COM} = 3.3 V; see FIG 7-5		38	47		95.2	ns	
t _{BBM}	Break-before-make time delay	R _L = 300 Ω, C _L = 35 pF, V _{NC} = V _{NO} = 3.3 V; see FIG 7-6		79		44		ns	
Q _C	Charge injection	V _{GEN} = V _{NC} = V _{NO} = 0 V, R _{GEN} = 0 Ω, C _L = 1 nF; see FIG 7-7		65				pC	
O _{ISO}	OFF isolation	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz, see FIG 7-8		−70				dB	
X _{TALK}	Channel-to-channel crosstalk	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz, see FIG 7-9		−70				dB	
BW	Bandwidth −3 dB	R _L = 50 Ω, see FIG 7-10		152				MHz	
THD	Total harmonic distortion	R _L = 600 Ω, C _L = 15 pF, V _{NO} = 1 VRMS, f = 20 kHz; see FIG 7-11		0.04%					
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	f = 1 MHz, see FIG 7-4		15				pF	
C _{COM(ON)} , C _{NC(ON)} , I _{NO(ON)}	COM, NC, NO ON capacitance	f = 1 MHz, see FIG 7-4		55				pF	
POWER REQUIREMENTS									
I _{CC}	Positive supply current	V _{IN} = 0 V or V _{CC}		0.02			1	μA	

(1) Specified by design, not subject to production test.

6.8 Typical Characteristics

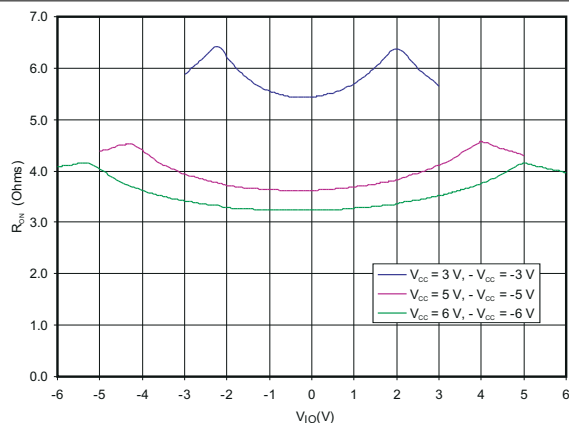


FIG 6-1. R_{ON} vs V_{IO}

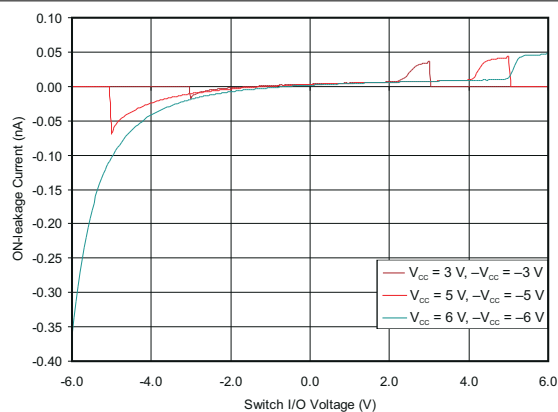


FIG 6-2. Leakage Current vs I/O Voltage (Switch ON)

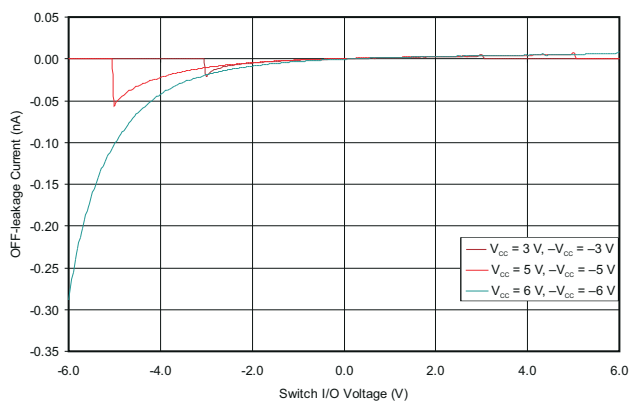


FIG 6-3. Leakage Current vs I/O Voltage (Switch OFF)

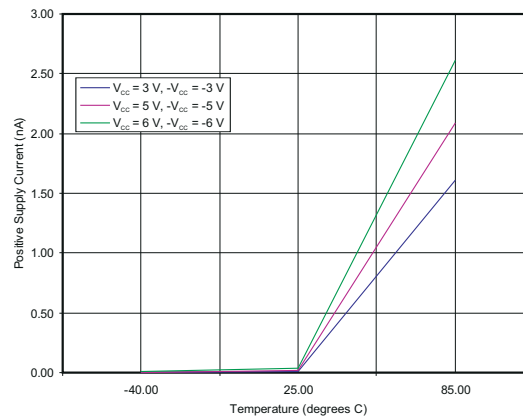


FIG 6-4. Positive Supply Current vs Temperature

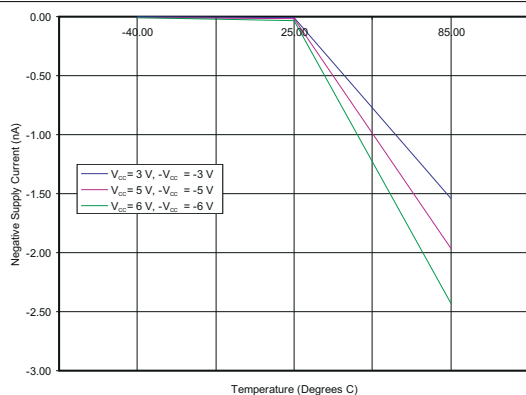


FIG 6-5. Negative Supply Current vs Temperature

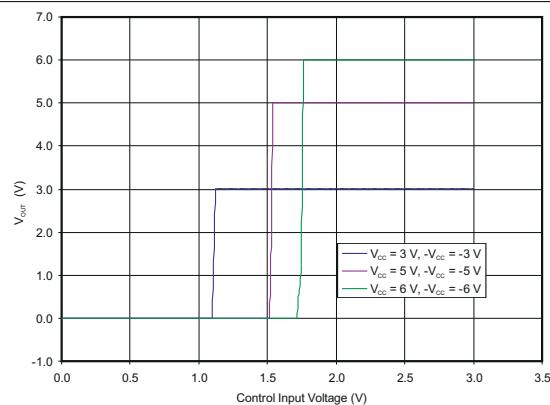


FIG 6-6. Control Input (IN) Threshold Voltage

6.8 Typical Characteristics (continued)

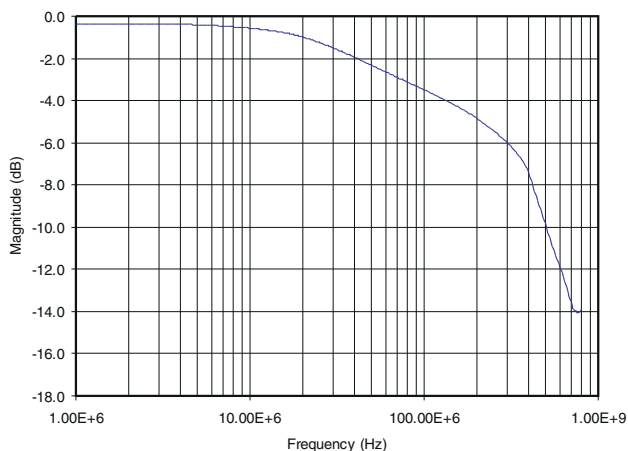


Figure 6-7. Bandwidth Dual Supply (± 5 V)

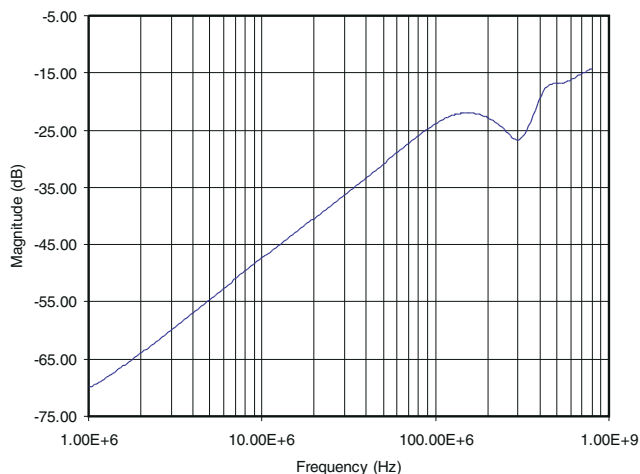


Figure 6-8. Off Isolation vs Frequency Dual Supply (± 5 V)

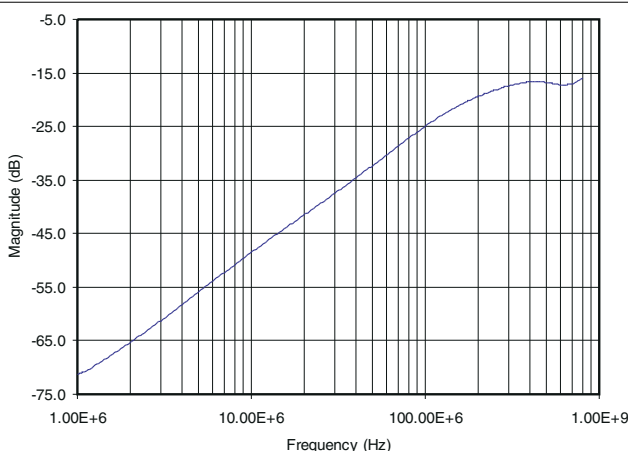


Figure 6-9. Crosstalk vs Frequency Dual Supply (± 5 V)

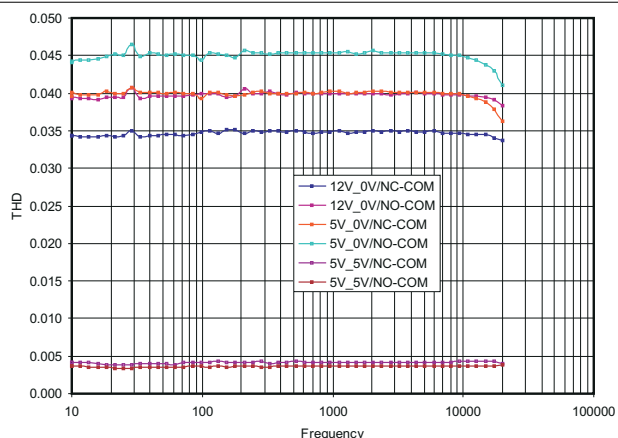


Figure 6-10. THD+N (%) vs Frequency

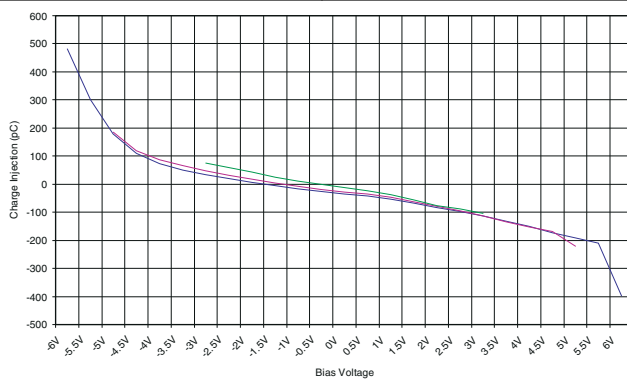
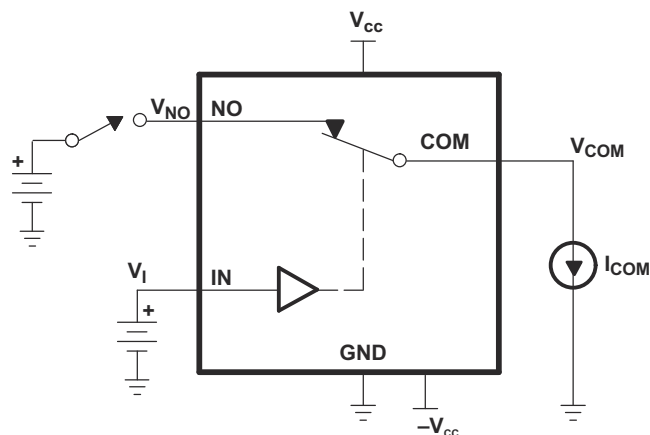


Figure 6-11. Charge Injection vs Bias Voltage

7 Parameter Measurement Information

7.1 Test Circuits

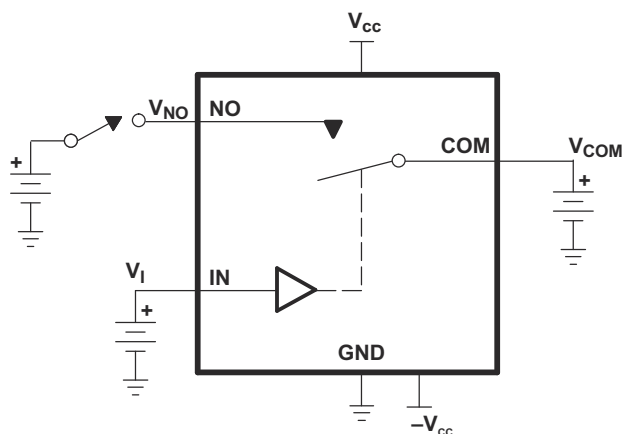


Channel ON

$$R_{on} = \frac{V_{COM} - V_{NO}}{I_{COM}}$$

$$V_I = V_{IH} \text{ or } V_{IL}$$

FIG 7-1. ON-State Resistance

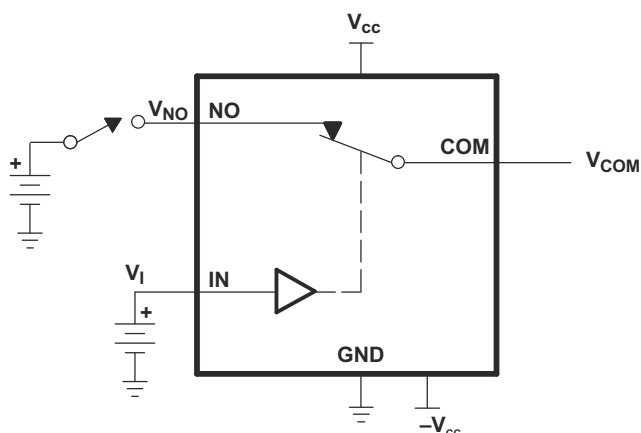


OFF-State Leakage Current

Channel OFF

$$V_I = V_{IH} \text{ or } V_{IL}$$

FIG 7-2. OFF-State Leakage Current ($I_{COM(OFF)}$, $I_{NC(OFF)}$)

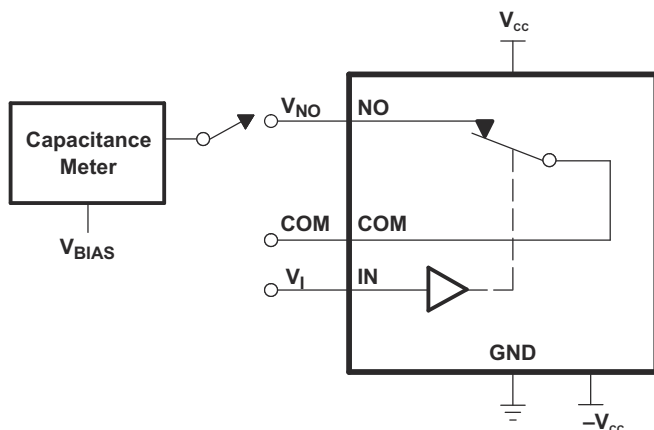


ON-State Leakage Current

Channel ON

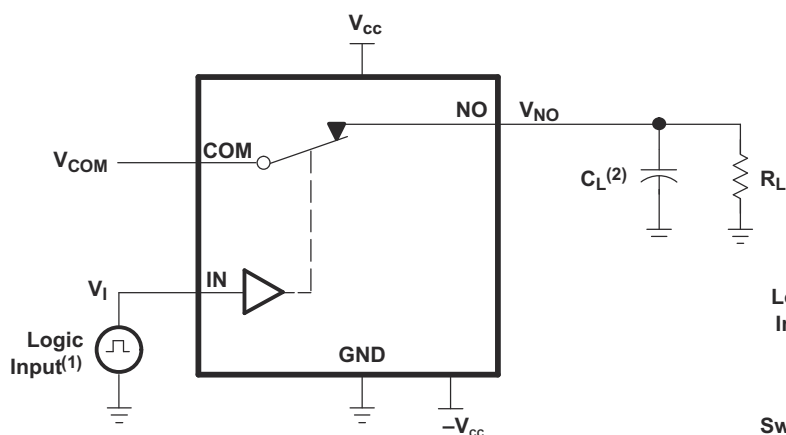
$$V_I = V_{IH} \text{ or } V_{IL}$$

FIG 7-3. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$)

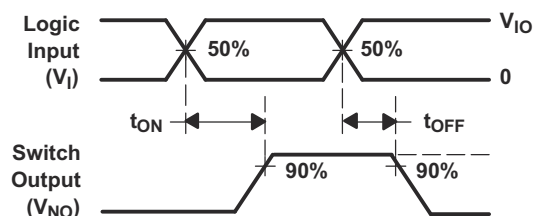


$V_{BIAS} = V_{CC}, V_{IO}, \text{ or GND}$
 $V_I = V_{IO} \text{ or GND}$
Capacitance is measured at NO, COM, and IN inputs during ON and OFF conditions.

7-4. Capacitance ($C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)

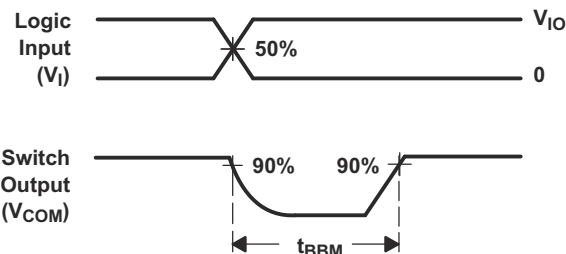
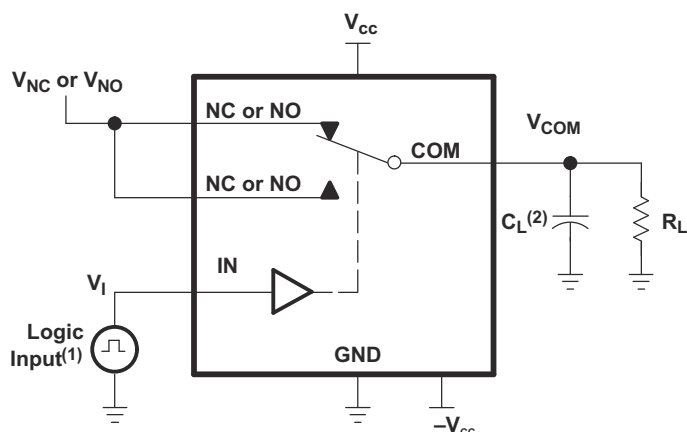


TEST	R_L	C_L	V_{COM}
t_{ON}	50 Ω	35 pF	V_{CC}
t_{OFF}	50 Ω	35 pF	V_{CC}



- (1) All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
(2) C_L includes probe and jig capacitance.

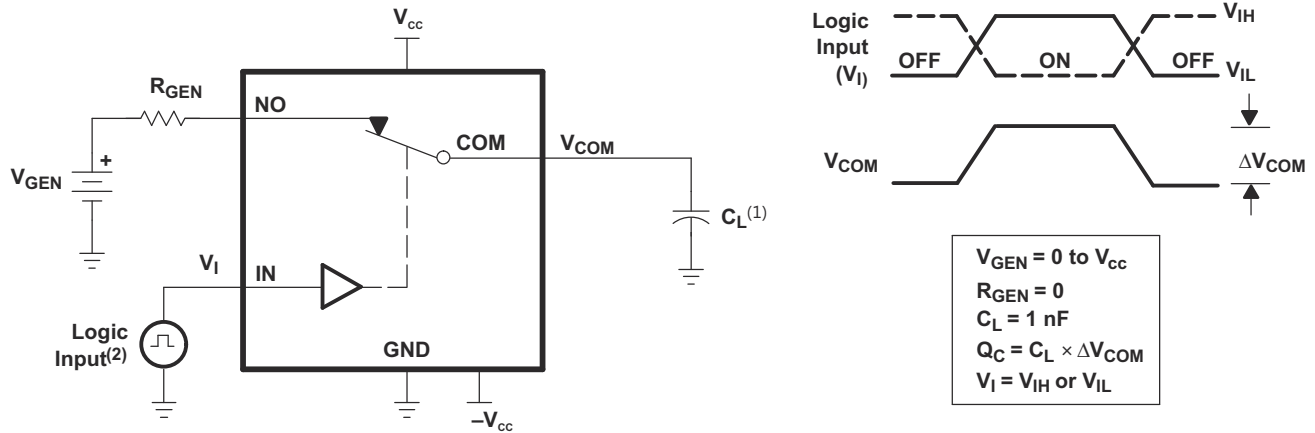
7-5. Turn-ON (t_{ON}) and Turn-OFF Time (t_{OFF})



$V_{NC} \text{ or } V_{NO} = V_{CC}/2$
 $R_L = 50 \Omega$
 $C_L = 35 \text{ pF}$

- (1) All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
(2) C_L includes probe and jig capacitance.

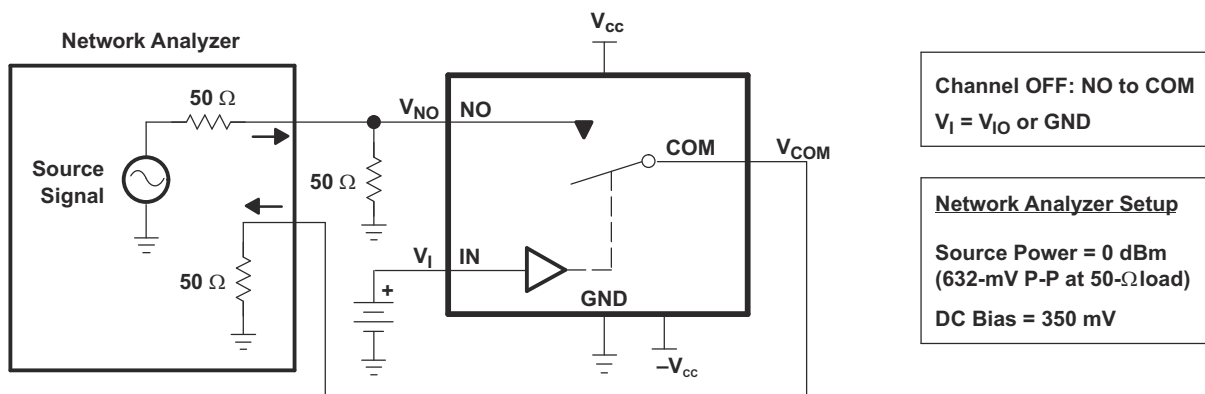
7-6. Break-Before-Make Time Delay (t_{BBM})



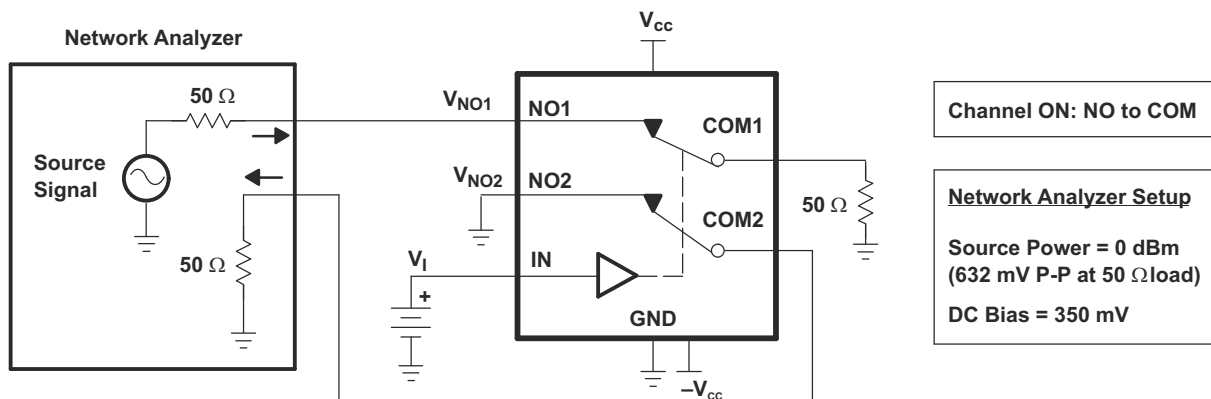
(1) C_L includes probe and jig capacitance.

(2) All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.

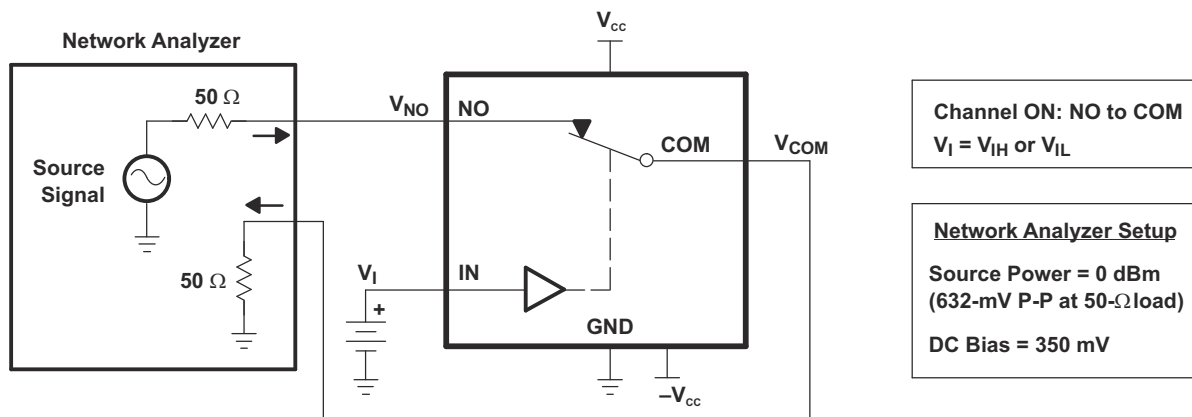
7-7. Charge Injection (Q_C)



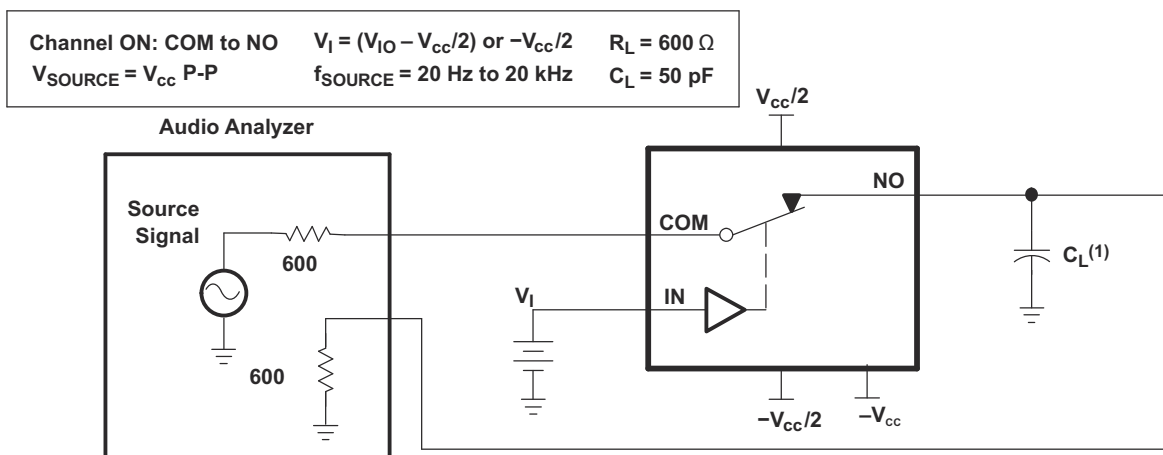
7-8. OFF Isolation (O_{ISO})



7-9. Channel-to-Channel Crosstalk (X_{TALK})



7-10. Bandwidth (BW)



(1) C_L includes probe and jig capacitance.

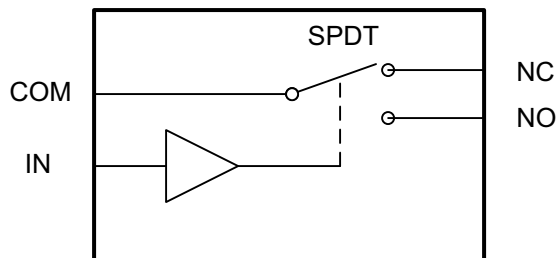
7-11. Total Harmonic Distortion

8 Detailed Description

8.1 Overview

The TS12A12511 is a bidirectional, single channel, single-pole double-throw (SPDT) analog switch that can pass signals with swings of 0 to 12 V or –6 V to 6 V. This switch conducts equally well in both directions when it is on. It also offers a low ON-state resistance of 5 Ω (typical), which is matched to within 1 Ω between channels. The maximum current consumption is < 1 μ A and –3 dB bandwidth is > 93 MHz. The TS12A12511 exhibits break-before-make switching action, preventing momentary shorting when switching channels. This device is available in an 8-lead MSOP, 8-lead SOT-23, and 8-pin QFN package.

8.2 Functional Block Diagram



8.3 Feature Description

The TS12A12511 can pass signals with swings of 0 to 12 V or –6 V to 6. The device is great for applications where the AC signals do not have a common mode voltage since both the positive and negative swing of the signal can be passed through the device with little distortion.

8.4 Device Functional Modes

表 8-1. Truth Table

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	On	Off
H	Off	On

9 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Application Information

Analog signals that range over the entire supply voltage (V_{CC} to GND) or (V_{CC} to $-V_{CC}$) can be passed with very little change in ON-state resistance. The switches are bidirectional, so the NO, NC, and COM pins can be used as either inputs or outputs.

9.2 Typical Application

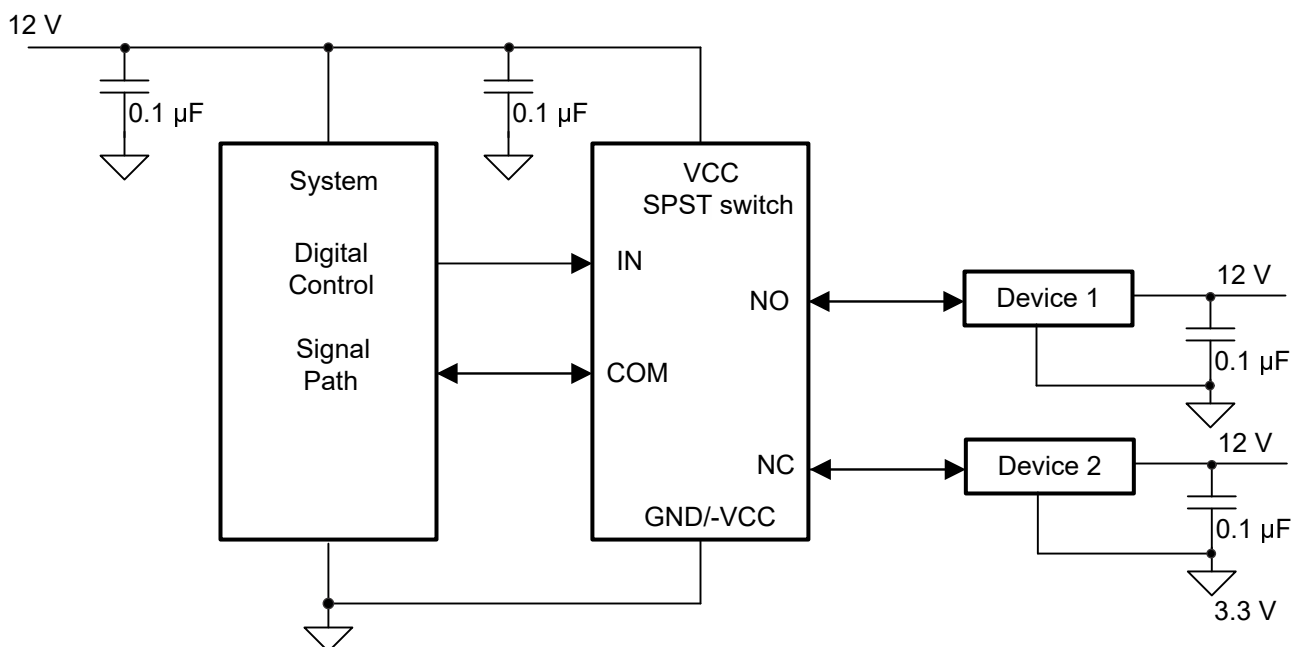


図 9-1. Typical Application Schematic

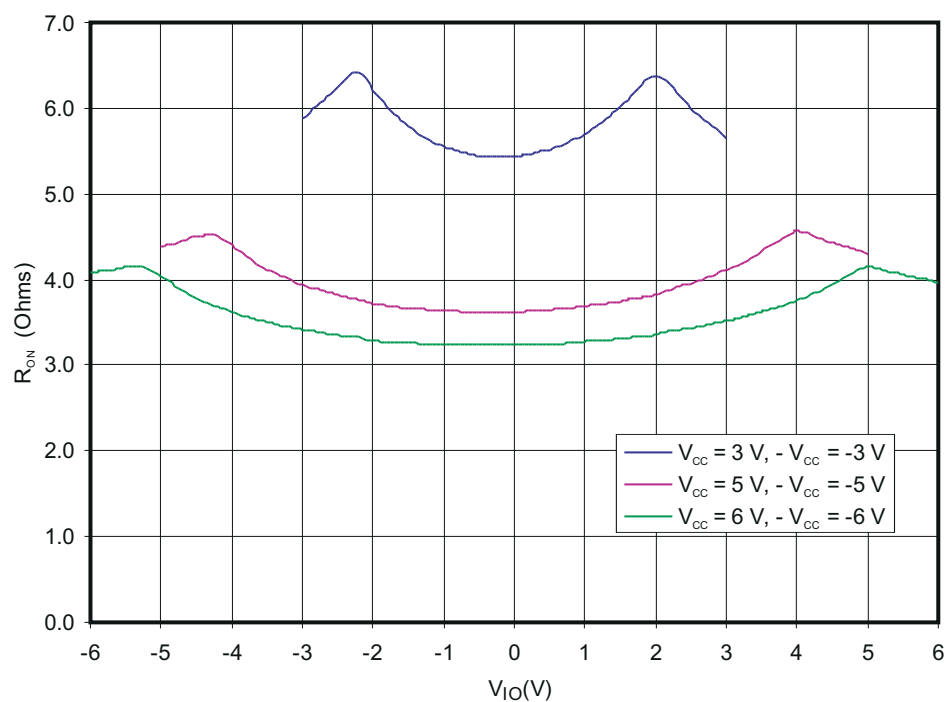
9.2.1 Design Requirements

Pull the digitally controlled input select pin IN to V_{CC} or GND to avoid unwanted switch states that could result if the logic control pin is left floating.

9.2.2 Detailed Design Procedure

Select the appropriate supply voltage to cover the entire voltage swing of the signal passing through the switch since the TS12A12511 input or output signal swing of the device is dependant of the supply voltage V_{CC} and $-V_{CC}$.

9.2.3 Application Curve



9-2. R_{ON} vs V_{IO}

10 Power Supply Recommendations

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings, because stresses beyond the listed ratings can cause permanent damage to the device. Always sequence VCC and -VCC on first, followed by NO, NC, or COM.

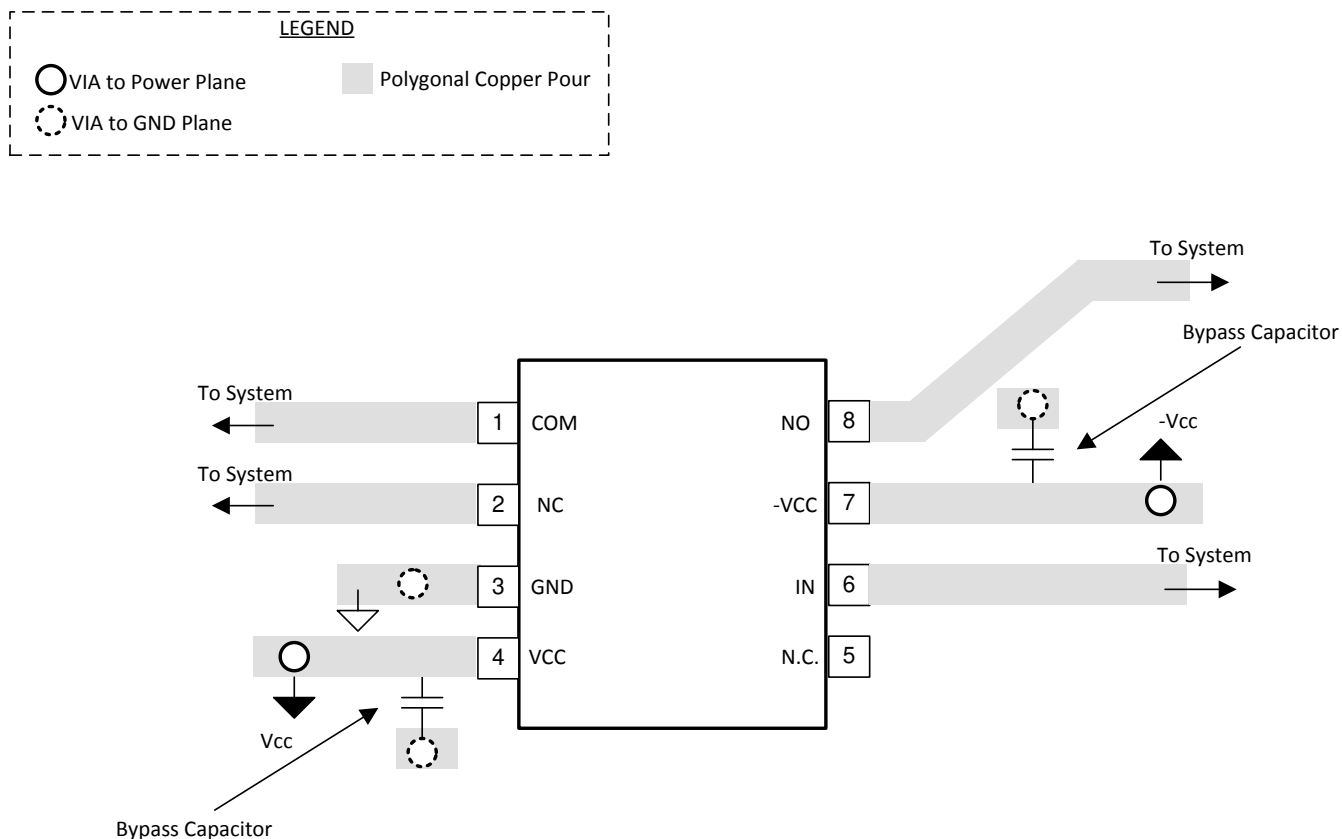
Although it is not required, power-supply bypassing improves noise margin and prevents switching noise propagation from the VCC supply to other components. A 0.1- μ F capacitor, connected from VCC to GND, is adequate for most applications.

11 Layout

11.1 Layout Guidelines

It is recommended to place a bypass capacitor as close to the supply pins, VCC and -VCC, as possible to help smooth out lower frequency noise and provide better load regulation across the frequency spectrum. Minimize trace lengths and vias on the signal paths to preserve signal integrity.

11.2 Layout Example



11-1. Layout Schematic

12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 サポート・リソース

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12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS12A12511DCNR	ACTIVE	SOT-23	DCN	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	NFHS NFHA	Samples
TS12A12511DGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	2US 2UA	Samples
TS12A12511DRJR	ACTIVE	SON	DRJ	8	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVE	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS12A12511DCNR	SOT-23	DCN	8	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
TS12A12511DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS12A12511DRJR	SON	DRJ	8	1000	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS

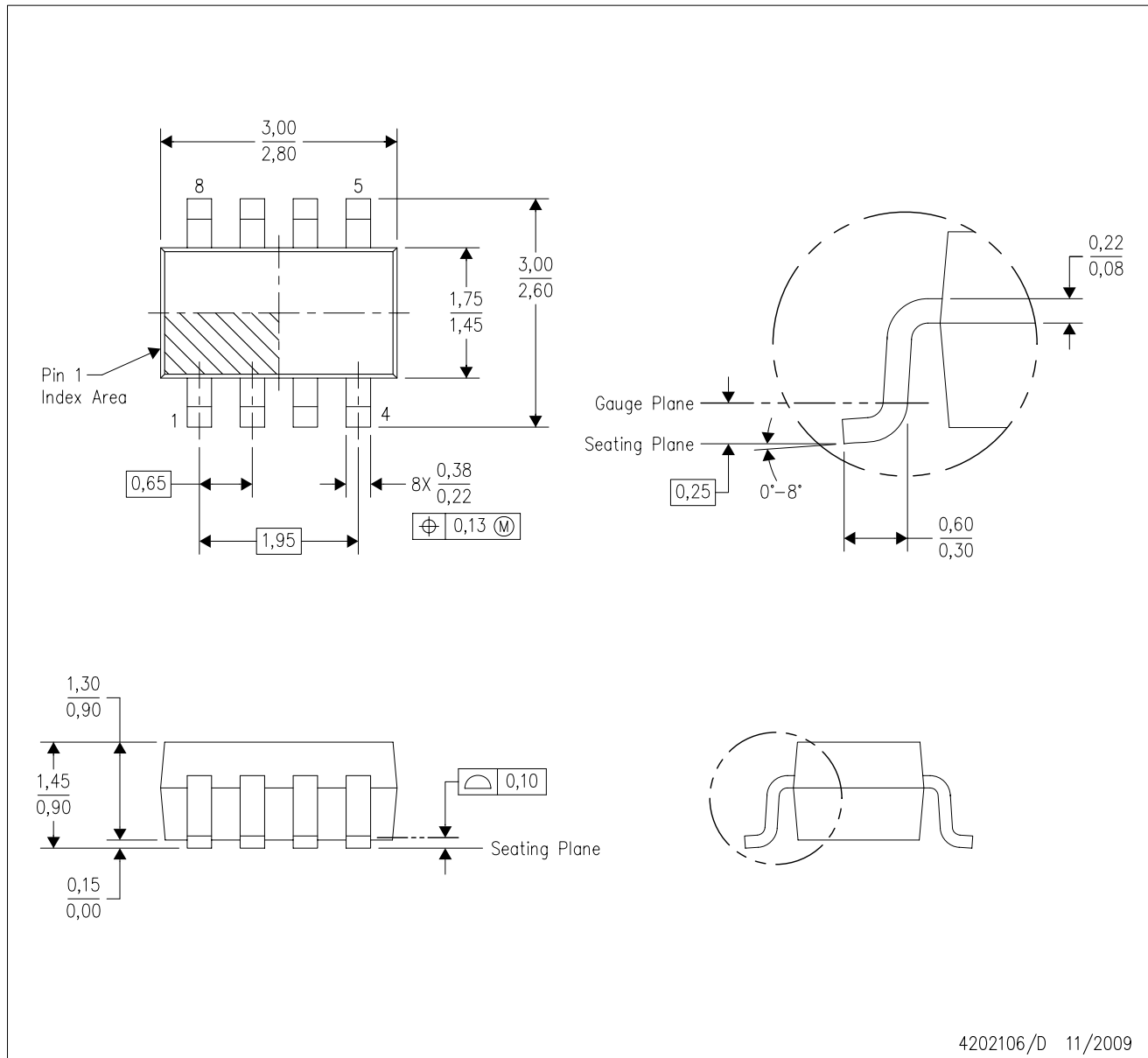


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS12A12511DCNR	SOT-23	DCN	8	3000	202.0	201.0	28.0
TS12A12511DGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
TS12A12511DRJR	SON	DRJ	8	1000	210.0	185.0	35.0

DCN (R-PDSO-G8)

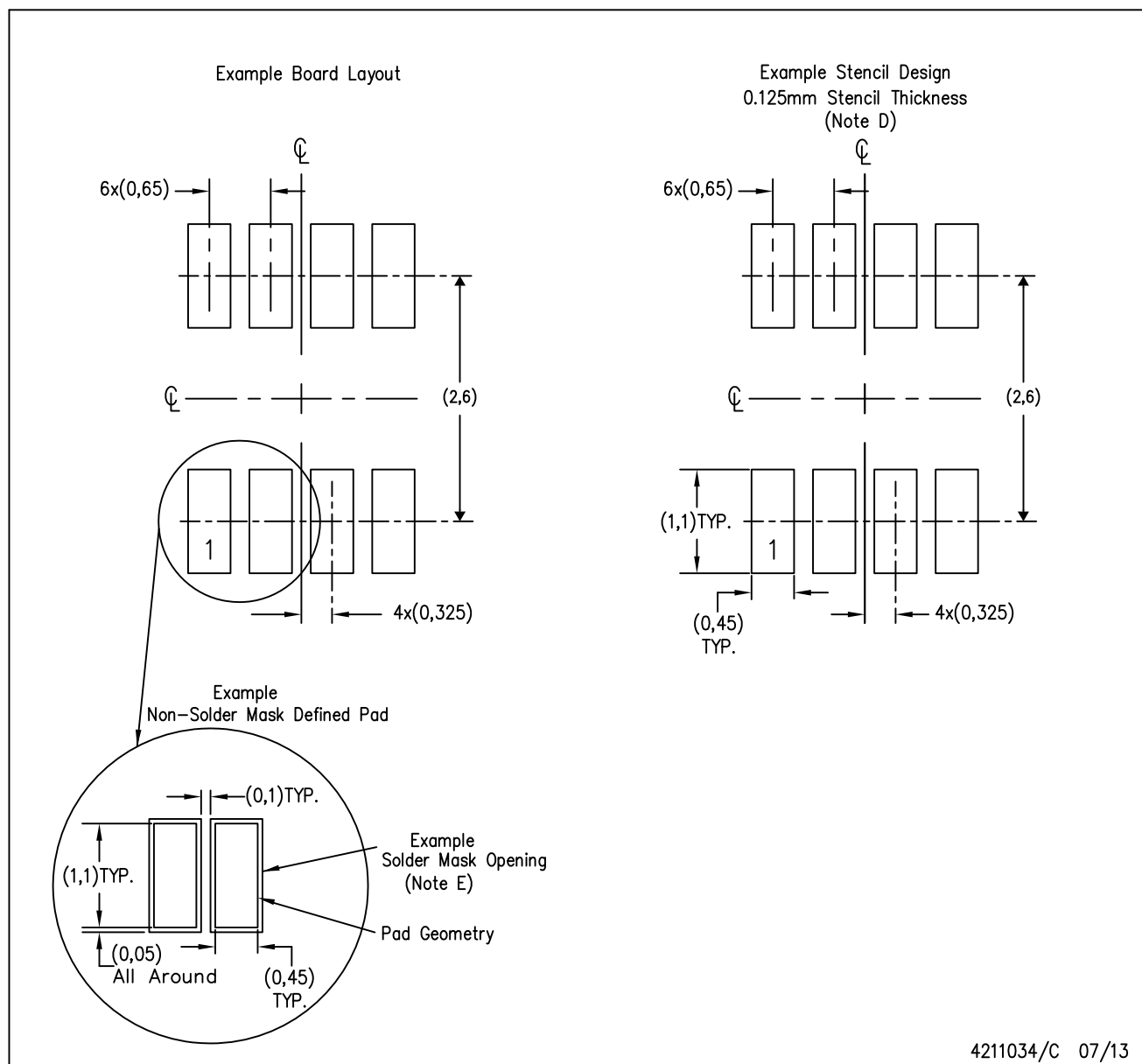
PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Package outline exclusive of metal burr & dambar protrusion/intrusion.
 - D. Package outline inclusive of solder plating.
 - E. A visual index feature must be located within the Pin 1 index area.
 - F. Falls within JEDEC MO-178 Variation BA.
 - G. Body dimensions do not include flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

DCN (R-PDSO-G8)

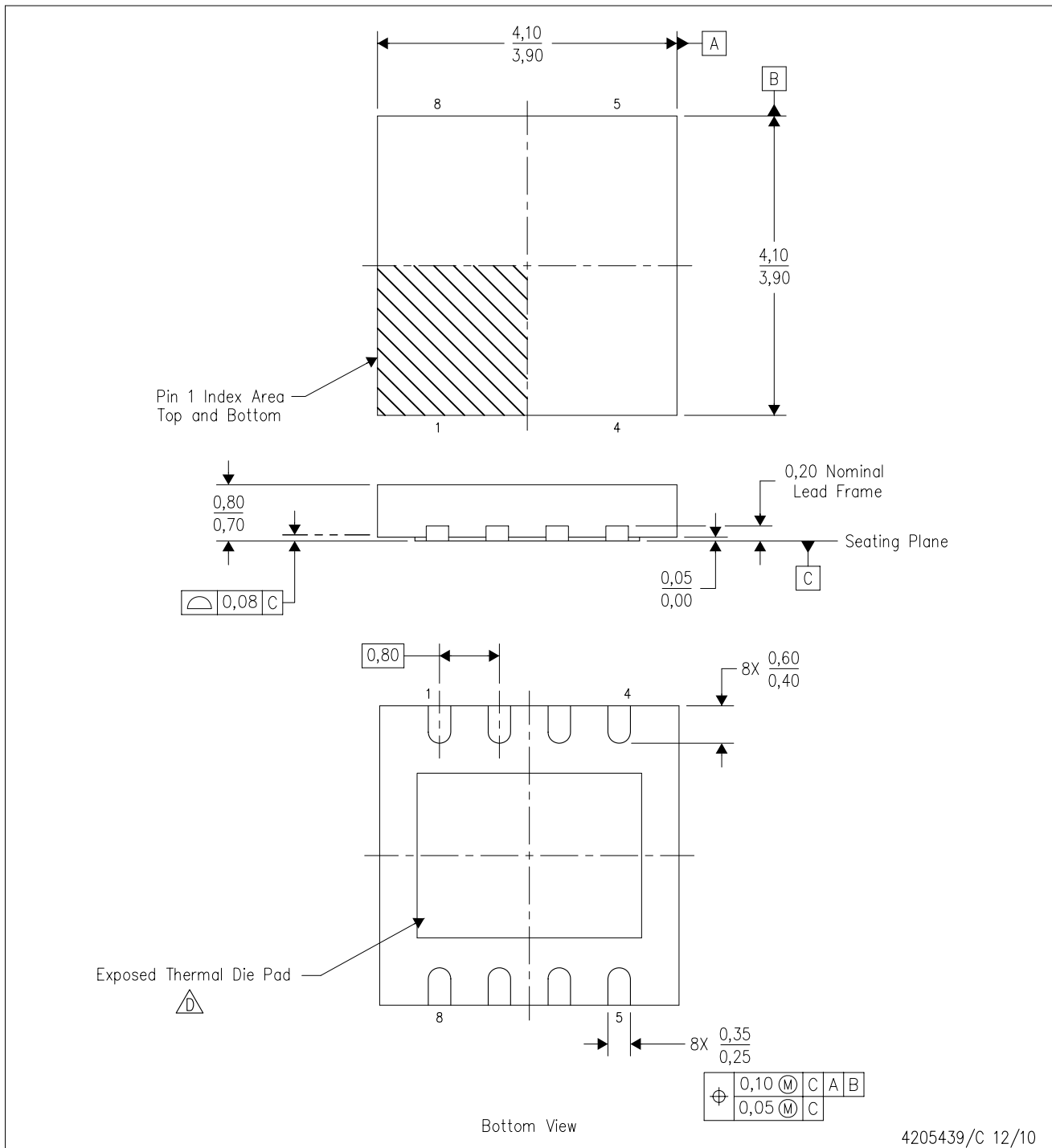
PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

DRJ (S-PWSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



4205439/C 12/10

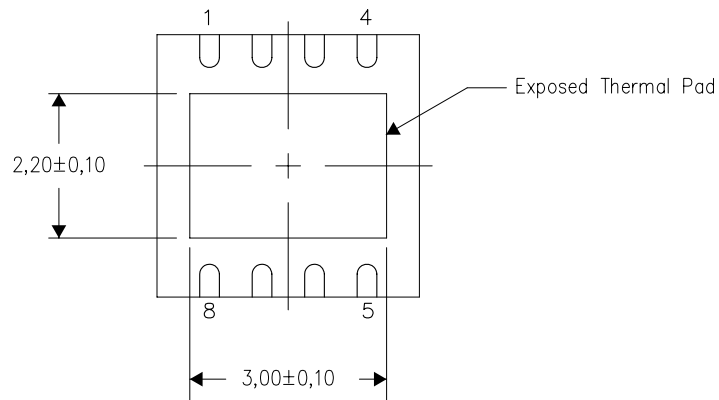
- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. SON (Small Outline No-Lead) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
 - E. Package complies to JEDEC MO-229 variation WGGB.

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

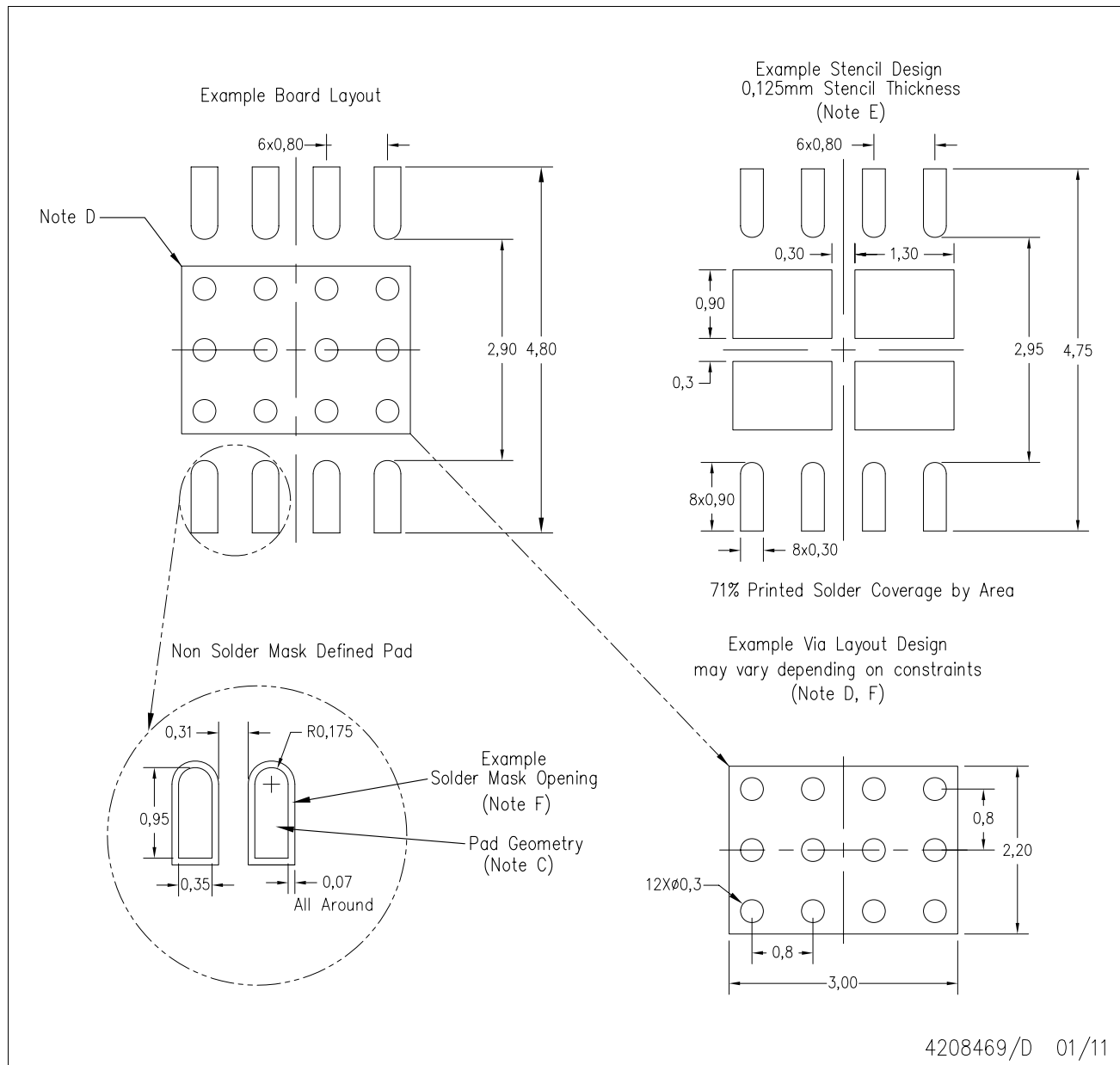
Exposed Thermal Pad Dimensions

4206882/F 01/11

NOTE: All linear dimensions are in millimeters

DRJ (S-PWSON-N8)

SMALL PACKAGE OUTLINE NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - E. Laser cutting apertures with electropolish and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - F. Customers should contact their board fabrication site for solder mask tolerances and vias tenting recommendations for vias placed in the thermal pad.

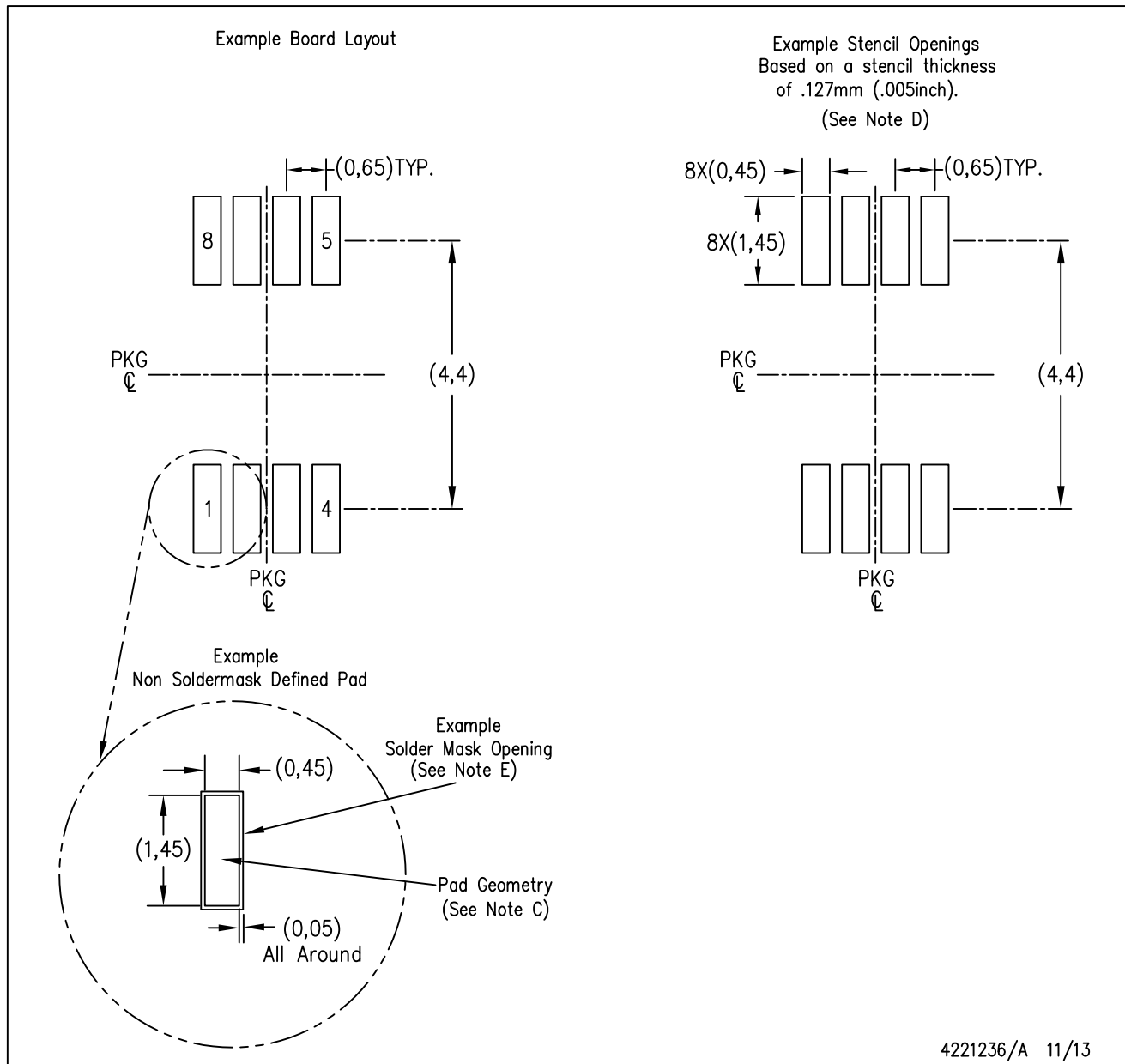
DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



4073329/E 05/06

- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
 - E. Falls within JEDEC MO-187 variation AA, except interlead flash.



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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